

Intelligent Power Module (IPM), 650 V, 30 A

NFAM3065L4BT

General Description

The NFAM3065L4BT is a fully-integrated inverter power module consisting of an independent High side gate driver, LVIC, six IGBT's and a temperature sensor (VTS or Thermistor (T)), suitable for driving permanent magnet synchronous (PMSM) motors, brushless DC (BLDC) motors and AC asynchronous motors. The IGBT's are configured in a three-phase bridge with separate emitter connections for the lower legs for maximum flexibility in the choice of control algorithm.

The power stage has undervoltage lockout protection (UVP). Internal boost diodes are provided for high side gate boost drive.

Features

- Three-phase 650 V, 30 A IGBT Module with Independent Drivers
- Active Logic Interface
- Built-in Undervoltage Protection (UVP)
- Integrated Bootstrap Diodes and Resistors
- Separate Low-side IGBT Emitter Connections for Individual Current Sensing of Each Phase
- Temperature Sensor (VTS or Thermistor (T))
- UL1557 Certified (File No.339285)
- This Device is Pb-Free and RoHS Compliant

Typical Applications

- Industrial Drives
- Industrial Pumps
- Industrial Fans
- Industrial Automation

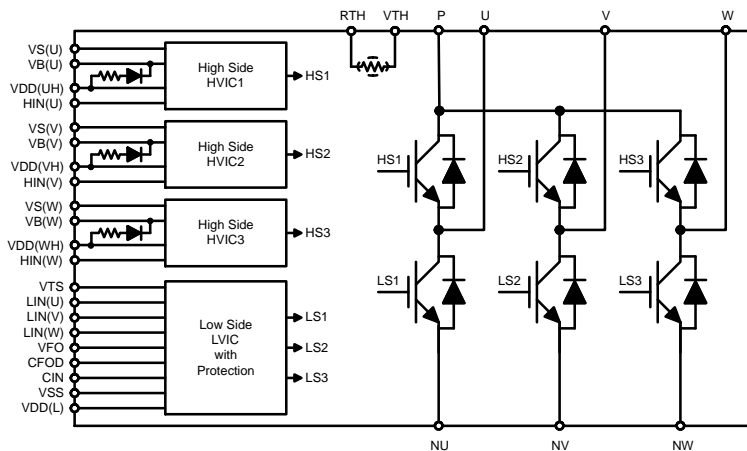
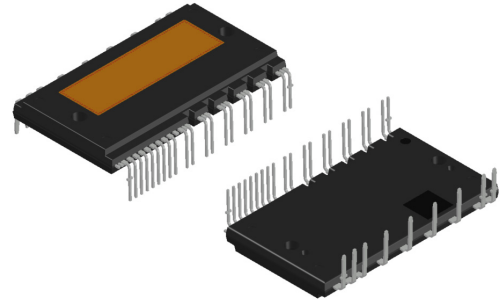


Figure 1. Application Schematic



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DIP39 54.5 x 31.0
CASE MODGC

MARKING DIAGRAM



Device marking is on package top side

NFAM3065L4BT = Specific Device Code
 ZZZ = Assembly Lot Code
 A = Assembly Location
 T = Test Location
 Y = Year
 WW = Work Week

ORDERING INFORMATION

| Device | Package | Shipping |
|--------------|-----------------------------------|----------|
| NFAM3065L4BT | DIP39 54.5 x 31.0 (Pb-Free) | 90 / Box |

NFAM3065L4BT

BLOCK DIAGRAM

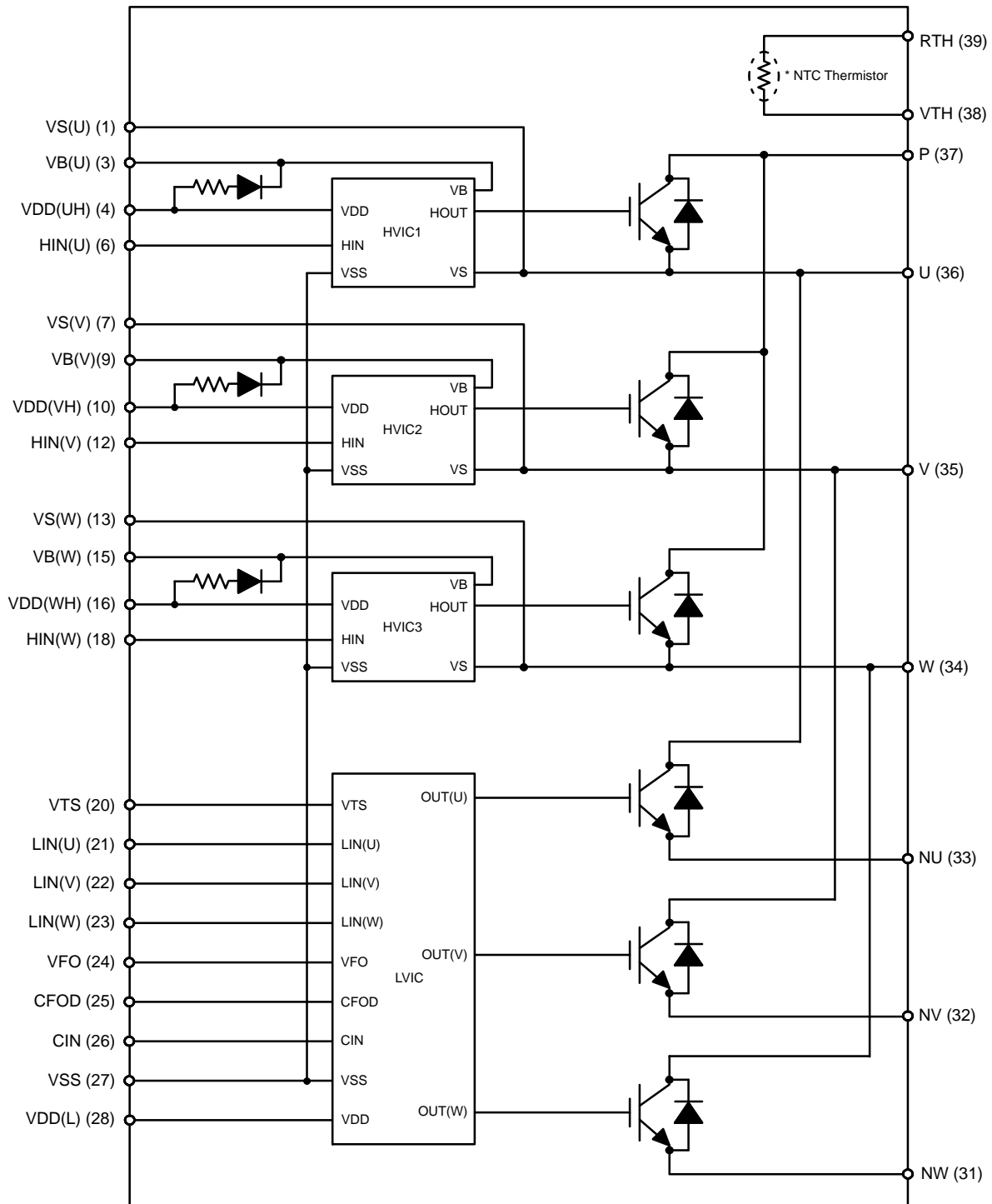


Figure 3. Equivalent Block Diagram

NFAM3065L4BT

PIN FUNCTION DESCRIPTION

| Pin | Name | Description |
|------|---------|--|
| 1 | VS(U) | High-Side Bias Voltage GND for U phase IGBT Driving |
| (2) | - | Dummy |
| 3 | VB(U) | High-Side Bias Voltage for U phase IGBT Driving |
| 4 | VDD(UH) | High-Side Bias Voltage for U phase IC |
| (5) | - | Dummy |
| 6 | HIN(U) | Signal Input for High-Side U Phase |
| 7 | VS(V) | High-Side Bias Voltage GND for V phase IGBT Driving |
| (8) | - | Dummy |
| 9 | VB(V) | High-Side Bias Voltage for V phase IGBT Driving |
| 10 | VDD(VH) | High-Side Bias Voltage for V phase IC |
| (11) | - | Dummy |
| 12 | HIN(V) | Signal Input for High-Side V Phase |
| 13 | VS(W) | High-Side Bias Voltage GND for W phase IGBT Driving |
| (14) | - | Dummy |
| 15 | VB(W) | High-Side Bias Voltage for W phase IGBT Driving |
| 16 | VDD(WH) | High-Side Bias Voltage for W phase IC |
| (17) | - | Dummy |
| 18 | HIN(W) | Signal Input for High-Side W Phase |
| (19) | - | Dummy |
| 20 | VTS | Voltage Output for LVIC Temperature Sensing Unit |
| 21 | LIN(U) | Signal Input for Low-Side U Phase |
| 22 | LIN(V) | Signal Input for Low-Side V Phase |
| 23 | LIN(W) | Signal Input for Low-Side W Phase |
| 24 | VFO | Fault Output |
| 25 | CFOD | Capacitor for Fault Output Duration Selection |
| 26 | CIN | Input for Current Protection |
| 27 | VSS | Low-Side Common Supply Ground |
| 28 | VDD(L) | Low-Side Bias Voltage for IC and IGBTs Driving |
| (29) | - | Dummy |
| (30) | - | Dummy |
| 31 | NW | Negative DC-Link Input for U Phase |
| 32 | NV | Negative DC-Link Input for V Phase |
| 33 | NU | Negative DC-Link Input for W Phase |
| 34 | W | Output for U Phase |
| 35 | V | Output for V Phase |
| 36 | U | Output for W Phase |
| 37 | P | Positive DC-Link Input |
| 38 | VTH | Thermistor Bias Voltage (T) / Not connection |
| 39 | RTH | Series Resistor for Thermistor (Temperature Detection) *optional for T |

1. Pins of () are the dummy for internal connection. These pins should be no connection.

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ABSOLUTE MAXIMUM RATINGS (T_C = 25°C) (Note 2)

| Symbol | Rating | Conditions | Value | Unit |
|------------|--|--|-------------|-------|
| VPN | Supply Voltage | P–NU, NV, NW | 450 | V |
| VPN(surge) | Supply Voltage (Surge) | P–NU, NV, NW (Note 3) | 550 | V |
| VPN(PROT) | Self Protection Supply Voltage Limit (Short-Circuit Protection Capability) | VDD = VBS = 13.5 V to 16.5 V, T _j = 150°C, VCES < 650 V, Non-Repetitive, < 2 μs | 400 | V |
| Vces | Collector-emitter Voltage | | 650 | V |
| VRRM | Maximum Repetitive Revers Voltage | | 650 | V |
| ±Ic | Each IGBT Collector Current | | ±30 | A |
| ±Icp | Each IGBT Collector Current (Peak) | Under 1ms Pulse Width | ±60 | A |
| VDD | Control Supply Voltage | VDD(UH,VH,WH), VDD(L)–VSS | –0.3 to 20 | V |
| VBS | High-Side Control Bias voltage | VB(U)–VS(U), VB(V)–VS(V), VB(W)–VS(W) | –0.3 to 20 | V |
| VIN | Input Signal Voltage | HIN(U), HIN(V), HIN(W), LIN(U), LIN(V), LIN(W)–VSS | –0.3 to VDD | V |
| VFO | Fault Output Supply Voltage | VFO–VSS | –0.3 to VDD | V |
| IFO | Fault Output Current | Sink Current at VFO pin | 2 | mA |
| VCIN | Current Sensing Input Voltage | CIN–VSS | –0.3 to VDD | V |
| Pc | Corrector Dissipation | Per One Chip | 113 | W |
| Tj | Operating Junction Temperature | | –40 to +150 | °C |
| Tstg | Storage Temperature | | –40 to +125 | °C |
| Tc | Module Case Operation Temperature | | –40 to +125 | °C |
| Viso | Isolation Voltage | 60 Hz, Sinusoidal, AC 1 minute, Connection Pins to Heat Sink Plate | 2500 | V rms |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

2. Refer to [ELECTRICAL CHARACTERISTICS](#), [RECOMMENDED OPERATING RANGES](#) and/or APPLICATION INFORMATION for Safe Operating parameters.

3. This surge voltage developed by the switching operation due to the wiring inductance between P and NU, NV, NW terminal.

THERMAL CHARACTERISTICS

| Symbol | Rating | Conditions | Min | Typ | Max | Unit |
|-----------------------|-------------------------------------|-------------------------------------|-----|-----|-----|------|
| R _{th(j-c)Q} | Junction-to-Case Thermal Resistance | Inverter IGBT Part (per 1/6 module) | – | – | 1.1 | °C/W |
| R _{th(j-c)F} | | Inverter FWD Part (per 1/6 module) | – | – | 2.2 | °C/W |

4. Refer to [ELECTRICAL CHARACTERISTICS](#), [RECOMMENDED OPERATING RANGES](#) and/or APPLICATION INFORMATION for Safe Operating parameters.

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RECOMMENDED OPERATING CONDITIONS

| Symbol | Rating | Conditions | Min | Typ | Max | Unit | |
|----------------------|-----------------------------|---|---------------|-----|------|------------|-------|
| VPN | Supply Voltage | P-NU, NV, NW | - | 300 | 400 | V | |
| VDD | Gate Driver Supply Voltages | VDD(UH,VH,WH), VDD(L)-VSS | 13.5 | 15 | 16.5 | V | |
| VBS | | VB(U)-VS(U), VB(V)-VS(V), VB(W)-VS(W) | 13.0 | 15 | 18.5 | V | |
| dVDD / dt, dVBS / dt | Supply Voltage Variation | | -1 | - | 1 | V/ μ s | |
| fPWM | PWM Frequency | | 1 | - | 20 | kHz | |
| DT | Dead Time | Turn-off to Turn-on (external) | 1.5 | - | - | μ s | |
| Io | Allowable r.m.s. Current | VPN = 300 V, VDD = 15 V, P.F. = 0.8, Tc \leq 125°C, Tj \leq 150°C (Note 5) | fPWM = 5 kHz | - | - | 25.7 | A rms |
| | | | fPWM = 15 kHz | - | - | 18.8 | |
| PWIN (on) | Allowable Input Pulse Width | 200 V \leq VPN \leq 400 V 13.5 V \leq VDD \leq 16.5 V 13.0 V \leq VBS \leq 18.5 V -20°C \leq Tc \leq 100°C | 1.0 | - | - | μ s | |
| PWIN (off) | | | 1.5 | - | - | | |
| | Package Mounting Torque | M3 type screw | 0.6 | 0.7 | 0.9 | Nm | |

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

5. Allowable r.m.s current depends on the actual conditions.

6. Flatness tolerance of the heatsink should be within -50 μ m to +100 μ m.

ELECTRICAL CHARACTERISTICS (T_C = 25°C, VDD = 15 V, VBS = 15 V, unless otherwise specified.) (Note 7)

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Unit |
|--------|-----------|-----------------|-----|-----|-----|------|
|--------|-----------|-----------------|-----|-----|-----|------|

INVERTER SECTION

| | | | | | | | |
|----------|--------------------------------------|-----------|---|------|------|------|---------|
| Ices | Collector-Emitter Leakage Current | | Vce = Vces, Tj = 25°C | - | - | 1 | mA |
| | | | Vce = Vces, Tj = 150°C | - | - | 10 | mA |
| VCE(sat) | Collector-Emitter Saturation Voltage | | VDD = VBS = 15 V, IN = 5 V Ic = 30 A, Tj = 25°C | - | 1.60 | 2.30 | V |
| | | | VDD = VBS = 15 V, IN = 5 V Ic = 30 A, Tj = 150°C | - | 1.80 | - | V |
| VF | FWDi Forward Voltage | | IN = 0 V, Ic = 30 A, Tj = 25°C | - | 2.00 | 2.40 | V |
| | | | IN = 0 V, Ic = 30 A, Tj = 150°C | - | 2.00 | - | V |
| ton | Switching Times | High Side | VPN = 300 V, VDD(H) = VDD(L) = 15 V Ic = 30 A, Tj = 25°C, IN = 0 \leftrightarrow 5 V Inductive Load | 0.80 | 1.25 | 1.85 | μ s |
| tc(on) | | | | - | 0.25 | 0.65 | μ s |
| toff | | | | - | 1.60 | 2.20 | μ s |
| tc(off) | | | | - | 0.25 | 0.75 | μ s |
| trr | | | | - | 0.15 | - | μ s |
| ton | | Low Side | | 0.80 | 1.40 | 2.00 | μ s |
| tc(on) | | | | - | 0.25 | 0.55 | μ s |
| toff | | | | - | 1.60 | 2.20 | μ s |
| tc(off) | | | | - | 0.25 | 0.75 | μ s |
| trr | | | | - | 0.10 | - | μ s |

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ELECTRICAL CHARACTERISTICS (T_C = 25°C, VDD = 15 V, VBS = 15 V, unless otherwise specified.) (Note 7) (continued)

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Unit | |
|-----------------------|--|---|---|-------|-------|------|----|
| DRIVER SECTION | | | | | | | |
| IQDDH | Quiescent VDD Supply Current | VDD(UH,VH,WH) = 15 V, HIN(U,V,W) = 0 V | VDD(UH)-VSS VDD(VH)-VSS VDD(WH)-VSS | - | - | 0.30 | mA |
| IQDDL | | VDD(L) = 15 V, LIN(U,V,W) = 0 V | VDD(L)-VSS | - | - | 3.50 | mA |
| IPDDH | Operating VCC Supply Current | VDD(UH,VH,WH) = 15 V, f _{PWM} = 20 kHz, Duty = 50%, Applied to one PWM Signal Input for High-Side | VDD(UH)-VSS VDD(VH)-VSS VDD(WH)-VSS | - | - | 0.40 | mA |
| IPDDL | | VDD(L) = 15 V, f _{PWM} = 20 kHz, Duty = 50%, Applied to one PWM Signal Input for Low-Side | VDD(L)-VSS | - | - | 6.00 | mA |
| IQBS | Quiescent VBS Supply Current | VBS = 15 V, HIN(U,V,W) = 0 V | VB(U)-VS(U) VB(V)-VS(V) VB(W)-VS(W) | - | - | 0.30 | mA |
| IPBS | Operating VBS Supply Current | VDD = VBS = 15 V, f _{PWM} = 20 kHz, Duty = 50%, Applied to one PWM Signal Input for High-Side | VB(U)-VS(U) VB(V)-VS(V) VB(W)-VS(W) | - | - | 5.00 | mA |
| VIN(ON) | ON Threshold Voltage | HIN(U,V,W)-VSS, LIN(U,V,W)-VSS | - | - | 2.6 | V | |
| VIN(OFF) | OFF Threshold Voltage | | 0.8 | - | - | V | |
| VCS(ref) | Short Circuit Trip Level | VDD = 15 V, CIN-VSS | 0.46 | 0.48 | 0.50 | V | |
| UVDDD | Supply Circuit Under-Voltage Protection | Detection Level | 10.3 | - | 12.5 | V | |
| UVDDR | | Reset Level | 10.8 | - | 13.0 | V | |
| UVBSD | | Detection Level | 10.0 | - | 12.0 | V | |
| UVBSR | | Reset Level | 10.5 | - | 12.5 | V | |
| VTS | Voltage Output for LVIC Temperature Sensing Unit | VTS-VSS = 10 nF, Temp. = 25°C | 0.905 | 1.030 | 1.155 | V | |
| VFOH | Fault Output Voltage | VDD = 0 V, CIN = 0 V, VFO Circuit: 10 kΩ to 5 V Pull-up | 4.9 | - | - | V | |
| VFOL | | VDD = 0 V, CIN = 1 V, VFO Circuit: 10 kΩ to 5 V Pull-up | - | - | 0.95 | V | |
| t _{FOD} | Fault-Output Pulse Width | CFOD = 22 nF | 1.6 | 2.4 | - | ms | |

BOOTSTRAP SECTION

| | | | | | | |
|-------|---------------------------------|------------|-----|-----|-----|---|
| VF | Bootstrap Diode Forward Voltage | If = 0.1 A | 3.4 | 4.6 | 5.8 | V |
| RBOOT | Built-in Limiting Resistance | | 30 | 38 | 46 | Ω |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- Performance guaranteed over the indicated operating temperature range by design and/or characterization tested at T_J = T_A = 25°C. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible.
- The fault-out pulse width t_{FOD} depends on the capacitance value of CFOD according to the following approximate equation:
t_{FOD} = 0.1 × 10⁶ × CFOD (s).
- Values based on design and/or characterization.

NFAM3065L4BT

Temperature of LVIC versus VTS Characteristics

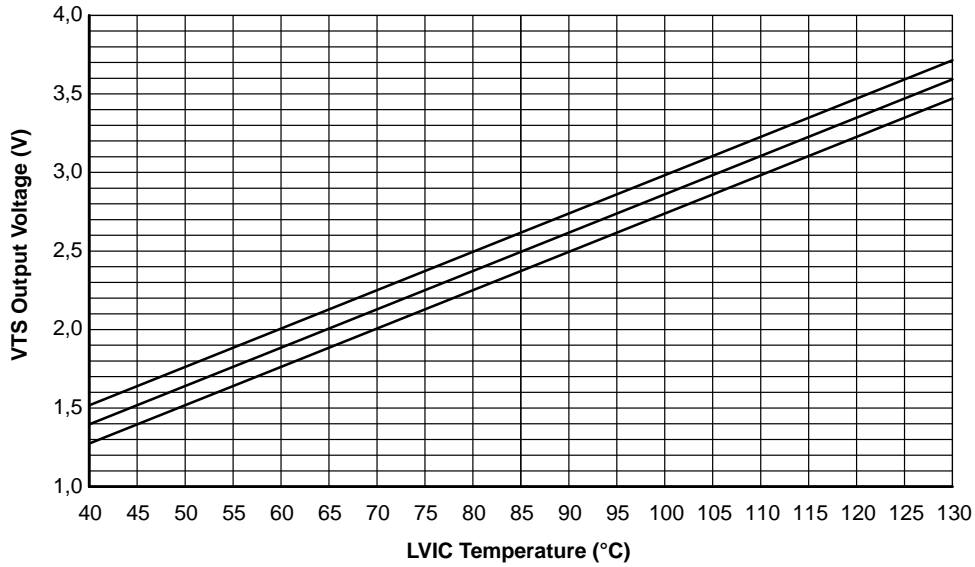


Figure 4. Temperature of LVIC versus VTS Characteristics

Table 1. THERMISTOR CHARACTERISTICS (INCLUDED ONLY IN NFAM3060L4BT)

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|----------------------|------------------|------------------------|--------|-------|--------|------|
| Resistance | R ₂₅ | T _c = 25°C | 46.530 | 47 | 47.47 | kΩ |
| Resistance | R ₁₂₅ | T _c = 100°C | 1.344 | 1.406 | 1.471 | kΩ |
| B-Constant (25–50°C) | – | B | 4009.5 | 4050 | 4090.5 | K |
| Temperature range | – | – | –40 | – | +125 | °C |

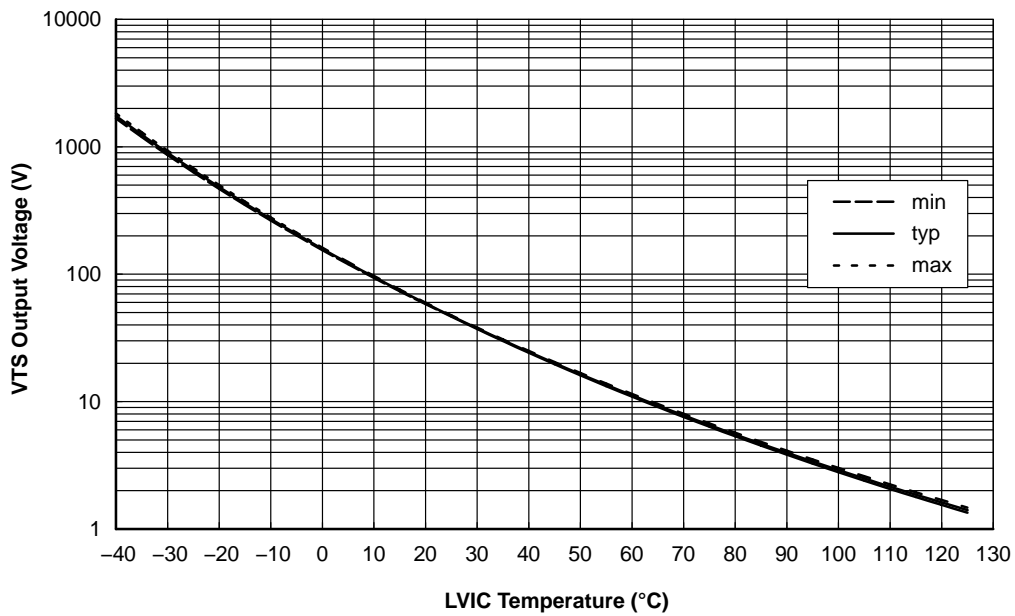
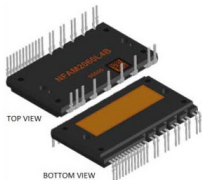


Figure 5. Thermistor Resistance versus Case Temperature

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



MINI DIP39, 31.0x54.5 CASE MODGC ISSUE A

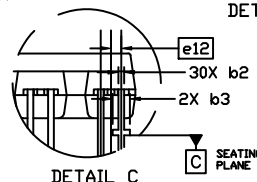
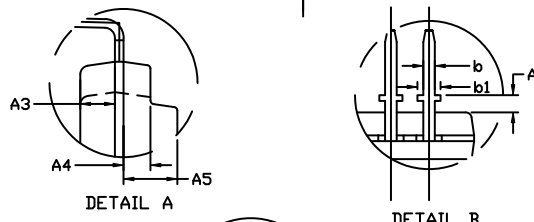
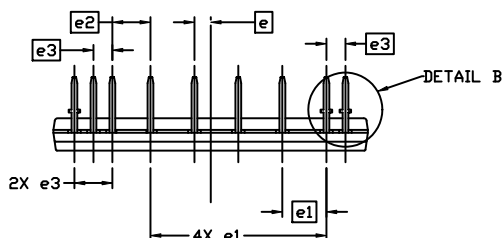
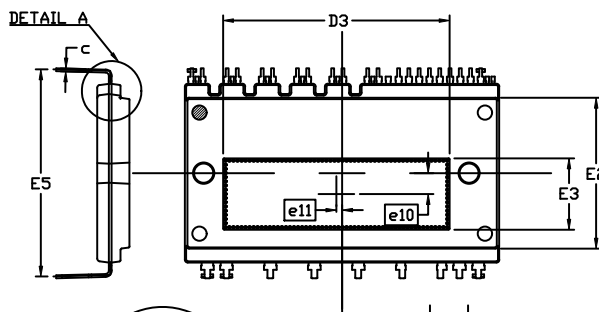
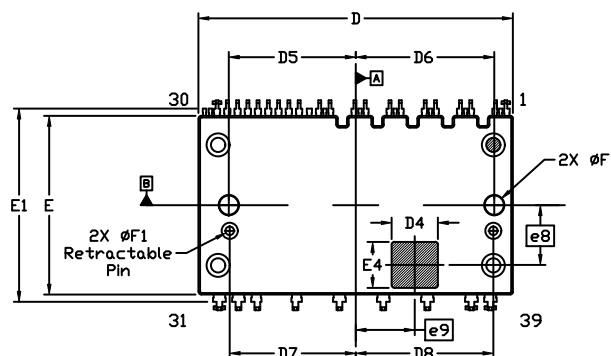
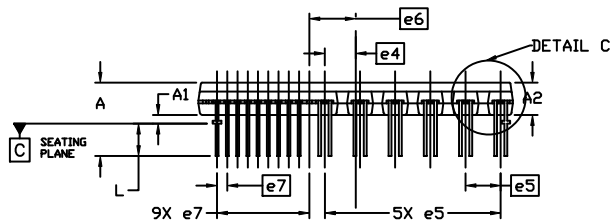
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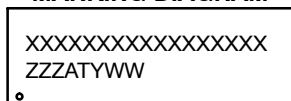
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSION *b* and *c* APPLY TO THE PLATED LEADS AND ARE MEASURED BETWEEN 1.00 AND 2.00 FROM THE LEAD TIP.
4. POSITION OF THE LEAD IS DETERMINED AT THE ROOT OF THE LEAD WHERE IT EXITS THE PACKAGE BODY.
5. SHORTENED/CUT PINS ARE 2,5,8,11,14,17,19,29 AND 30.

| MILLIMETERS | | | |
|-------------|-----------|-------|-------|
| DIM | MIN. | NOM. | MAX. |
| A | 12.20 | 12.7 | 13.2 |
| A1 | 1.00 | 1.50 | 2.00 |
| A2 | 5.50 | 5.60 | 5.70 |
| A3 | 2.00 REF | | |
| A4 | 1.55 REF | | |
| A5 | 3.10 REF | | |
| b | 0.90 | 1.00 | 1.10 |
| b1 | 1.90 | 2.00 | 2.10 |
| b2 | 0.40 | 0.50 | 0.60 |
| b3 | 1.40 | 1.50 | 1.60 |
| c | 0.50 REF | | |
| D | 54.40 | 54.50 | 54.60 |
| D3 | 39.25 REF | | |
| D4 | 8.00 REF | | |
| D5 | 22.00 REF | | |
| D6 | 24.00 REF | | |
| D7 | 21.85 REF | | |
| D8 | 23.85 REF | | |

| MILLIMETERS | | | |
|-------------|-----------|-------|-------|
| DIM | MIN. | NOM. | MAX. |
| E | 30.90 | 31.00 | 31.10 |
| E1 | 33.50 REF | | |
| E2 | 26.14 REF | | |
| E3 | 12.35 REF | | |
| E4 | 8.00 REF | | |
| E5 | 35.40 | 35.90 | 36.40 |
| e | 2.81 REF | | |
| e1 | 7.62 BSC | | |
| e2 | 6.60 BSC | | |
| e3 | 3.30 BSC | | |
| e4 | 5.35 REF | | |
| e5 | 6.10 BSC | | |
| e6 | 8.02 REF | | |
| e7 | 1.78 BSC | | |
| e8 | 10.35 REF | | |
| e9 | 10.25 REF | | |
| e10 | 3.60 REF | | |
| e11 | 1.00 REF | | |
| e12 | 0.89 BSC | | |
| F | 3.20 | 3.30 | 3.40 |
| F1 | 1.40 | 1.50 | 1.60 |
| L | 5.60 REF | | |



GENERIC MARKING DIAGRAM*



- XXXXX = Specific Device Code
- ZZZ = Assembly Lot Code
- AT = Assembly & Test Location
- Y = Year
- WW = Work Week

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

| | | |
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| DESCRIPTION: | MINI DIP39, 31.0x54.5 | PAGE 1 OF 1 |

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